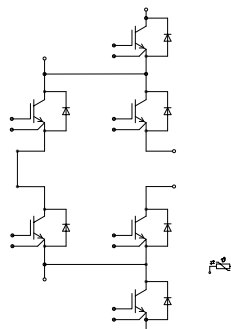
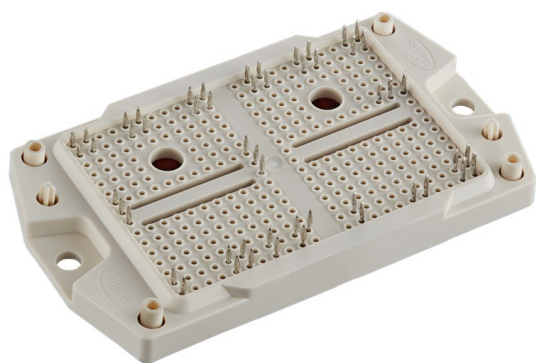


EasyPACK™ Modul mit TRENCHSTOP™ IGBT7 und CoolSiC™ Schottky Diode und PressFIT / NTC
 EasyPACK™ module with TRENCHSTOP™ IGBT7 and CoolSiC™ Schottky diode and PressFIT / NTC



$V_{CES} = 950V$
 $I_{C\ nom} = 400A / I_{CRM} = 800A$

Potentielle Anwendungen

- 3-Level-Applikationen
- Solar Anwendungen

Elektrische Eigenschaften

- CoolSiC™ Schottky Diode Gen 5
- Niederinduktives Design
- Niedrige Schaltverluste
- Trenchstop™ IGBT7

Mechanische Eigenschaften

- Gehäuse mit CTI > 400
- Integrierter NTC Temperatur Sensor
- PressFIT Verbindungstechnik

Potential Applications

- 3-level-applications
- Solar applications

Electrical Features

- CoolSiC™ Schottky diode gen 5
- Low inductive design
- Low switching losses
- Trenchstop™ IGBT7

Mechanical Features

- Package with CTI > 400
- Integrated NTC temperature sensor
- PressFIT contact technology

Module Label Code

Barcode Code 128



DMX - Code



Content of the Code

Content of the Code	Digit
Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

IGBT, T1 / T4 / IGBT, T1 / T4

Höchstzulässige Werte / Maximum Rated Values

Kollektor-Emitter-Sperrspannung Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	950	V
Implementierter Kollektor-Strom Implemented collector current		I_{CN}	400	A
Kollektor-Dauergleichstrom Continuous DC collector current	$T_H = 65^{\circ}\text{C}, T_{vj\text{max}} = 175^{\circ}\text{C}$	I_{CDC}	220	A
Periodischer Kollektor-Spitzenstrom Repetitive peak collector current	$t_p = 1\text{ ms}$	I_{CRM}	800	A
Gate-Emitter-Spitzenspannung Gate-emitter peak voltage		V_{GES}	+/-20	V

Charakteristische Werte / Characteristic Values

		min.	typ.	max.	
Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage	$I_C = 150\text{ A}$ $V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{sat}}$	1,40 1,48 1,50	1,60 V V V
Gate-Schwellenspannung Gate threshold voltage	$I_C = 6,50\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		V_{GETH}	4,35	5,10 5,85 V
Gateladung Gate charge	$V_{GE} = -15 / 15\text{ V}, V_{CE} = 600\text{ V}$		Q_G	0,90	μC
Interner Gatewiderstand Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		R_{Gint}	0,75	Ω
Eingangskapazität Input capacitance	$f = 100\text{ kHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{ies}	25,2	nF
Rückwirkungskapazität Reverse transfer capacitance	$f = 100\text{ kHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{res}	0,078	nF
Kollektor-Emitter-Reststrom Collector-emitter cut-off current	$V_{CE} = 950\text{ V}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$	I_{CES}		0,071 mA
Gate-Emitter-Reststrom Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}		100 nA
Einschaltverzögerungszeit, induktive Last Turn-on delay time, inductive load	$I_C = 150\text{ A}, V_{CE} = 500\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Gon} = 5,0\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{don}	0,094 0,094 0,094	μs μs μs
Anstiegszeit, induktive Last Rise time, inductive load	$I_C = 150\text{ A}, V_{CE} = 500\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Gon} = 5,0\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_r	0,033 0,033 0,033	μs μs μs
Abschaltverzögerungszeit, induktive Last Turn-off delay time, inductive load	$I_C = 150\text{ A}, V_{CE} = 500\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Goff} = 20\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{doff}	0,74 0,81 0,82	μs μs μs
Fallzeit, induktive Last Fall time, inductive load	$I_C = 150\text{ A}, V_{CE} = 500\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Goff} = 20\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_f	0,033 0,057 0,07	μs μs μs
Einschaltverlustenergie pro Puls Turn-on energy loss per pulse	$I_C = 150\text{ A}, V_{CE} = 500\text{ V}, L\sigma = 35\text{ nH}$ $di/dt = 4200\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $V_{GE} = -15 / 15\text{ V}, R_{Gon} = 5,0\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{on}	4,30 4,30 4,30	mJ mJ mJ
Abschaltverlustenergie pro Puls Turn-off energy loss per pulse	$I_C = 150\text{ A}, V_{CE} = 500\text{ V}, L\sigma = 35\text{ nH}$ $du/dt = 4600\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $V_{GE} = -15 / 15\text{ V}, R_{Goff} = 20\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{off}	5,00 6,60 7,30	mJ mJ mJ
Kurzschlußverhalten SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 600\text{ V}$ $V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$	$t_p \leq 0\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$	I_{SC}	1200	A
Wärmewiderstand, Chip bis Kühlkörper Thermal resistance, junction to heatsink	pro IGBT / per IGBT		R_{thJH}	0,240	K/W
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\text{op}}$	-40	150 $^{\circ}\text{C}$

IGBT, T2 / T3 / IGBT, T2 / T3

Höchstzulässige Werte / Maximum Rated Values

Kollektor-Emitter-Sperrspannung Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	950	V
Implementierter Kollektor-Strom Implemented collector current		I_{CN}	400	A
Kollektor-Dauergleichstrom Continuous DC collector current	$T_H = 65^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	I_{CDC}	295	A
Periodischer Kollektor-Spitzenstrom Repetitive peak collector current	$t_p = 1\text{ ms}$	I_{CRM}	800	A
Gate-Emitter-Spitzenspannung Gate-emitter peak voltage		V_{GES}	+/-20	V

Charakteristische Werte / Characteristic Values

				min.	typ.	max.	
Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage	$I_C = 150\text{ A}$ $V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{ sat}}$		1,07 1,04 1,02	1,15	V V V
Gate-Schwellenspannung Gate threshold voltage	$I_C = 6,50\text{ mA}, V_{CE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		V_{GETH}	4,15	4,90	5,65	V
Gateladung Gate charge	$V_{GE} = -15 / 15\text{ V}, V_{CE} = 600\text{ V}$		Q_G		4,10		μC
Interner Gatewiderstand Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		R_{Gint}		0,75		Ω
Eingangskapazität Input capacitance	$f = 100\text{ kHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{ies}		49,2		nF
Rückwirkungskapazität Reverse transfer capacitance	$f = 100\text{ kHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{res}		0,228		nF
Kollektor-Emitter-Reststrom Collector-emitter cut-off current	$V_{CE} = 950\text{ V}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$	I_{CES}			0,071	mA
Gate-Emitter-Reststrom Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}			100	nA
Einschaltverzögerungszeit, induktive Last Turn-on delay time, inductive load	$I_C = 150\text{ A}, V_{CE} = 500\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Gon} = 5,0\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{don}		0,21 0,19 0,18		μs μs μs
Anstiegszeit, induktive Last Rise time, inductive load	$I_C = 150\text{ A}, V_{CE} = 500\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Gon} = 5,0\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_r		0,034 0,038 0,039		μs μs μs
Abschaltverzögerungszeit, induktive Last Turn-off delay time, inductive load	$I_C = 150\text{ A}, V_{CE} = 500\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Goff} = 5,0\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{doff}		0,85 0,96 0,98		μs μs μs
Fallzeit, induktive Last Fall time, inductive load	$I_C = 150\text{ A}, V_{CE} = 500\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Goff} = 5,0\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_f		0,24 0,45 0,50		μs μs μs
Einschaltverlustenergie pro Puls Turn-on energy loss per pulse	$I_C = 150\text{ A}, V_{CE} = 500\text{ V}, L\sigma = 35\text{ nH}$ $di/dt = 4500\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $V_{GE} = -15 / 15\text{ V}, R_{Gon} = 5,0\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{on}		3,35 3,46 3,49		mJ mJ mJ
Abschaltverlustenergie pro Puls Turn-off energy loss per pulse	$I_C = 150\text{ A}, V_{CE} = 500\text{ V}, L\sigma = 35\text{ nH}$ $du/dt = 1350\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $V_{GE} = -15 / 15\text{ V}, R_{Goff} = 5,0\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{off}		24,8 35,6 37,9		mJ mJ mJ
Kurzschlußverhalten SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 600\text{ V}$ $V_{CEmax} = V_{CES} - L_{SCE} \cdot di/dt$	$t_p \leq 0\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$	I_{SC}		1200		A
Wärmewiderstand, Chip bis Kühlkörper Thermal resistance, junction to heatsink	pro IGBT / per IGBT		R_{thJH}		0,280		K/W
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\text{ op}}$	-40		150	$^{\circ}\text{C}$

IGBT, T5 / T6 / IGBT, T5 / T6

Höchstzulässige Werte / Maximum Rated Values

Kollektor-Emitter-Sperrspannung Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	950	V
Implementierter Kollektor-Strom Implemented collector current		I_{CN}	200	A
Kollektor-Dauergleichstrom Continuous DC collector current	$T_H = 65^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	I_{CDC}	115	A
Periodischer Kollektor-Spitzenstrom Repetitive peak collector current	$t_p = 1\text{ ms}$	I_{CRM}	400	A
Gate-Emitter-Spitzenspannung Gate-emitter peak voltage		V_{GES}	+/-20	V

Charakteristische Werte / Characteristic Values

				min.	typ.	max.	
Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage	$I_C = 150\text{ A}$ $V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{ sat}}$		1,68 1,88 1,92	2,00	V V V
Gate-Schwellenspannung Gate threshold voltage	$I_C = 3,25\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		V_{GETH}	4,35	5,10	5,85	V
Gateladung Gate charge	$V_{GE} = -15 / 15\text{ V}, V_{CE} = 600\text{ V}$		Q_G		0,45		μC
Interner Gatewiderstand Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		R_{Gint}		1,5		Ω
Eingangskapazität Input capacitance	$f = 100\text{ kHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{ies}		12,6		nF
Rückwirkungskapazität Reverse transfer capacitance	$f = 100\text{ kHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{res}		0,039		nF
Kollektor-Emitter-Reststrom Collector-emitter cut-off current	$V_{CE} = 950\text{ V}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$	I_{CES}			0,1	mA
Gate-Emitter-Reststrom Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}			100	nA
Einschaltverzögerungszeit, induktive Last Turn-on delay time, inductive load	$I_C = 150\text{ A}, V_{CE} = 500\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Gon} = 5,0\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{don}		0,086 0,093 0,094		μs μs μs
Anstiegszeit, induktive Last Rise time, inductive load	$I_C = 150\text{ A}, V_{CE} = 500\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Gon} = 5,0\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_r		0,027 0,03 0,03		μs μs μs
Abschaltverzögerungszeit, induktive Last Turn-off delay time, inductive load	$I_C = 150\text{ A}, V_{CE} = 500\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Goff} = 30\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{doff}		0,57 0,615 0,625		μs μs μs
Fallzeit, induktive Last Fall time, inductive load	$I_C = 150\text{ A}, V_{CE} = 500\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Goff} = 30\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_f		0,024 0,052 0,073		μs μs μs
Einschaltverlustenergie pro Puls Turn-on energy loss per pulse	$I_C = 150\text{ A}, V_{CE} = 500\text{ V}, L\sigma = 35\text{ nH}$ $di/dt = 4000\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $V_{GE} = -15 / 15\text{ V}, R_{Gon} = 5,0\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{on}		6,35 7,60 8,00		mJ mJ mJ
Abschaltverlustenergie pro Puls Turn-off energy loss per pulse	$I_C = 150\text{ A}, V_{CE} = 500\text{ V}, L\sigma = 35\text{ nH}$ $du/dt = 5800\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $V_{GE} = -15 / 15\text{ V}, R_{Goff} = 30\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{off}		5,00 6,30 6,80		mJ mJ mJ
Kurzschlußverhalten SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 600\text{ V}$ $V_{CE\max} = V_{CES} - L_{SCE} \cdot di/dt$	$t_p \leq 0\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$	I_{SC}		600		A
Wärmewiderstand, Chip bis Kühlkörper Thermal resistance, junction to heatsink	pro IGBT / per IGBT		R_{thJH}		0,451		K/W
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\text{ op}}$	-40		150	$^{\circ}\text{C}$

Diode, D1 / D4 / Diode, D1 / D4

Höchstzulässige Werte / Maximum Rated Values

Periodische Spitzenspannung Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	950	V
Implementierter Durchlassstrom Implemented forward current		I_{FN}	200	A
Dauergleichstrom Continuous DC forward current		I_F	150	A
Periodischer Spitzenstrom Repetitive peak forward current	$t_p = 1\text{ ms}$	I_{FRM}	400	A
Grenzlastintegral I^2t - value	$V_R = 0\text{ V}, t_p = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$ $V_R = 0\text{ V}, t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I^2t	1620 1530	A^2s A^2s

Charakteristische Werte / Characteristic Values

			min.	typ.	max.	
Durchlassspannung Forward voltage	$I_F = 150\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$	V_F	2,33	2,54	V
	$I_F = 150\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 125^{\circ}\text{C}$		2,12		V
	$I_F = 150\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 150^{\circ}\text{C}$		2,08		V
Rückstromspitze Peak reverse recovery current	$I_F = 150\text{ A}, -di_F/dt = 4000\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 500\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$	I_{RM}	90,0		A
		$T_{vj} = 125^{\circ}\text{C}$		130		A
		$T_{vj} = 150^{\circ}\text{C}$		140		A
Sperrverzögerungsladung Recovered charge	$I_F = 150\text{ A}, -di_F/dt = 4000\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 500\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$	Q_r	5,50		μC
		$T_{vj} = 125^{\circ}\text{C}$		10,0		μC
		$T_{vj} = 150^{\circ}\text{C}$		12,5		μC
Abschaltenergie pro Puls Reverse recovery energy	$I_F = 150\text{ A}, -di_F/dt = 4000\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 500\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$	E_{rec}	1,50		mJ
		$T_{vj} = 125^{\circ}\text{C}$		3,30		mJ
		$T_{vj} = 150^{\circ}\text{C}$		3,95		mJ
Wärmewiderstand, Chip bis Kühlkörper Thermal resistance, junction to heatsink	pro Diode / per diode	R_{thJH}		0,570		K/W
Temperatur im Schaltbetrieb Temperature under switching conditions		$T_{vj\text{ op}}$	-40		150	$^{\circ}\text{C}$

Diode, D2 / D3 / Diode, D2 / D3

Höchstzulässige Werte / Maximum Rated Values

Periodische Spitzenspannung Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	950	V
Implementierter Durchlassstrom Implemented forward current		I_{FN}	200	A
Dauergleichstrom Continuous DC forward current		I_F	150	A
Periodischer Spitzenstrom Repetitive peak forward current	$t_p = 1\text{ ms}$	I_{FRM}	400	A
Grenzlastintegral I^2t - value	$V_R = 0\text{ V}, t_p = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$ $V_R = 0\text{ V}, t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I^2t	1620 1530	A^2s A^2s

Charakteristische Werte / Characteristic Values

			min.	typ.	max.	
Durchlassspannung Forward voltage	$I_F = 150\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$	V_F	2,33	2,54	V
	$I_F = 150\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 125^{\circ}\text{C}$		2,12		V
	$I_F = 150\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 150^{\circ}\text{C}$		2,06		V
Rückstromspitze Peak reverse recovery current	$I_F = 150\text{ A}, -di_F/dt = 4500\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 500\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$	I_{RM}	133		A
		$T_{vj} = 125^{\circ}\text{C}$		180		A
		$T_{vj} = 150^{\circ}\text{C}$		195		A
Sperrverzögerungsladung Recovered charge	$I_F = 150\text{ A}, -di_F/dt = 4500\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 500\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$	Q_r	6,00		μC
		$T_{vj} = 125^{\circ}\text{C}$		13,0		μC
		$T_{vj} = 150^{\circ}\text{C}$		15,5		μC
Abschaltenergie pro Puls Reverse recovery energy	$I_F = 150\text{ A}, -di_F/dt = 4500\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 500\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$	E_{rec}	2,40		mJ
		$T_{vj} = 125^{\circ}\text{C}$		5,70		mJ
		$T_{vj} = 150^{\circ}\text{C}$		6,80		mJ
Wärmewiderstand, Chip bis Kühlkörper Thermal resistance, junction to heatsink	pro Diode / per diode	R_{thJH}		0,570		K/W
Temperatur im Schaltbetrieb Temperature under switching conditions		$T_{vj\text{ op}}$	-40		150	$^{\circ}\text{C}$

Diode, D5-D6 / Diode, D5-D6

Höchstzulässige Werte / Maximum Rated Values

Periodische Spitzenspernung Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1200	V
Dauergleichstrom Continuous DC forward current		I_F	100	A
Periodischer Spitzenstrom Repetitive peak forward current	$t_p = 1\text{ ms}$	I_{FRM}	200	A
Grenzlastintegral I^2t - value	$V_R = 0\text{ V}, t_p = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$ $V_R = 0\text{ V}, t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I^2t	1650 1550	A^2s A^2s

Charakteristische Werte / Characteristic Values

			min.	typ.	max.	
Durchlassspannung Forward voltage	$I_F = 100\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 100\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 100\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	V_F	1,45 1,75 1,85	1,75	V V V
Rückstromspitze Peak reverse recovery current	$I_F = 100\text{ A}, -di_F/dt = 3200\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 500\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	I_{RM}	60,0 60,0 60,0		A A A
Sperrverzögerungsladung Recovered charge	$I_F = 100\text{ A}, -di_F/dt = 3200\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 500\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	Q_r	1,85 1,85 1,85		μC μC μC
Abschaltenergie pro Puls Reverse recovery energy	$I_F = 100\text{ A}, -di_F/dt = 3200\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 500\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{rec}	0,68 0,68 0,68		mJ mJ mJ
Wärmewiderstand, Chip bis Kühlkörper Thermal resistance, junction to heatsink	pro Diode / per diode		R_{thJH}	0,474		K/W
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150	$^{\circ}\text{C}$

NTC-Widerstand / NTC-Thermistor

Charakteristische Werte / Characteristic Values

			min.	typ.	max.	
Nennwiderstand Rated resistance	$T_{NTC} = 25^{\circ}\text{C}$		R_{25}	5,00		k Ω
Abweichung von R100 Deviation of R100	$T_{NTC} = 100^{\circ}\text{C}, R_{100} = 493\ \Omega$		$\Delta R/R$	-5	5	%
Verlustleistung Power dissipation	$T_{NTC} = 25^{\circ}\text{C}$		P_{25}		20,0	mW
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298,15\text{ K}))]$		$B_{25/50}$	3375		K
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298,15\text{ K}))]$		$B_{25/80}$	3411		K
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298,15\text{ K}))]$		$B_{25/100}$	3433		K

Angaben gemäß gültiger Application Note.
Specification according to the valid application note.

Modul / Module

Isolations-Prüfspannung Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V _{ISOL}	3,2		kV
Innere Isolation Internal isolation	Basisisolierung (Schutzklasse 1, EN61140) basic insulation (class 1, IEC 61140)		Al ₂ O ₃		
Kriechstrecke Creepage distance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal		11,5 6,8		mm
Luftstrecke Clearance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal		9,4 5,5		mm
Vergleichszahl der Kriechwegbildung Comperative tracking index		CTI	> 400		
Relativer Temperaturindex (elektr.) RTI Elec.	Gehäuse housing	RTI	140		°C
			min.	typ.	max.
Modulstreuinduktivität Stray inductance module		L _{sCE}		15	nH
Lagertemperatur Storage temperature		T _{stg}	-40		125 °C
Anzugsdrehmoment f. Modulmontage Mounting torque for modul mounting	Schraube - Montage gem. gültiger Applikationsschrift Screw - Mounting according to valid application note	M	1,30		1,50 Nm
Gewicht Weight		G		78	g

Der Strom im Dauerbetrieb ist auf 25 A effektiv pro Anschlusspin begrenzt.

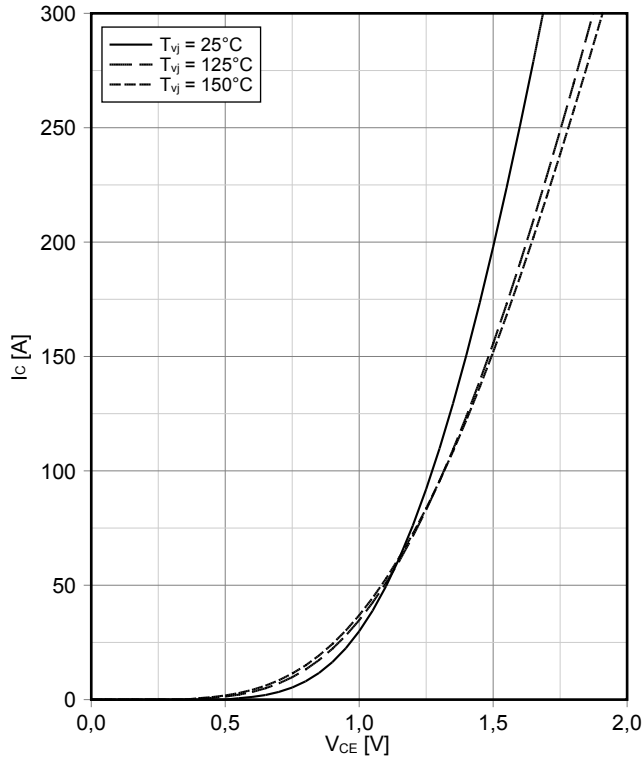
The current under continuous operation is limited to 25 A rms per connector pin.

IGBT- und Dioden-RthJH-Parameter mit einer Wärmeleitpaste $\lambda_{\text{Paste}} = 3.3 \text{ W/(m}\cdot\text{K)}$ gemessen

IGBT- and diode- RthJH parameters measured with thermal grease of $\lambda_{\text{Paste}} = 3.3 \text{ W/(m}\cdot\text{K)}$

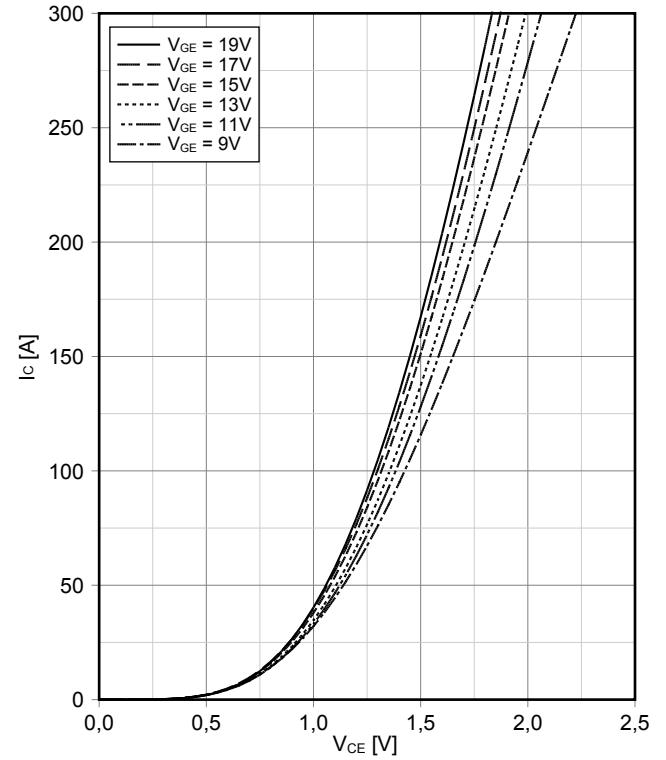
Ausgangskennlinie IGBT, T1 / T4 (typisch)
output characteristic IGBT, T1 / T4 (typical)

$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



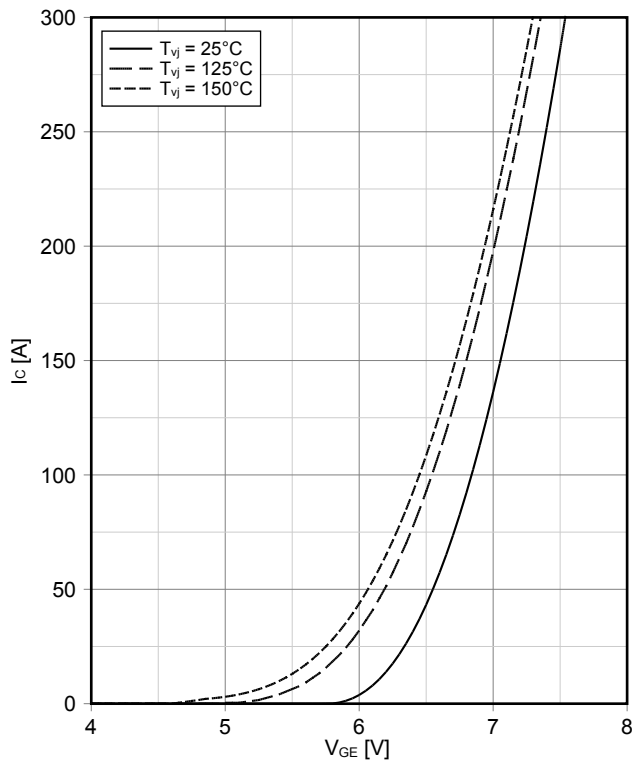
Ausgangskennlinienfeld IGBT, T1 / T4 (typisch)
output characteristic IGBT, T1 / T4 (typical)

$I_C = f(V_{CE})$
 $T_{vj} = 150^\circ\text{C}$



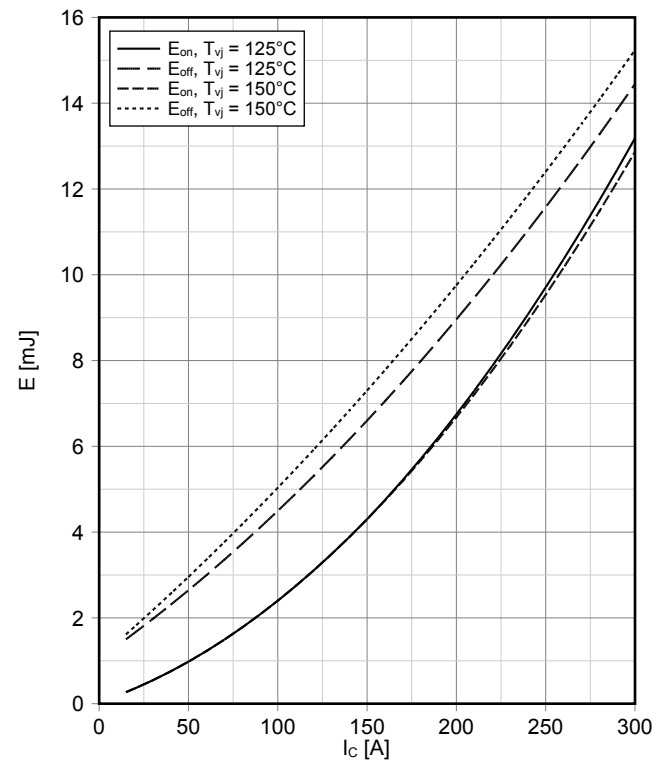
Übertragungscharakteristik IGBT, T1 / T4 (typisch)
transfer characteristic IGBT, T1 / T4 (typical)

$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



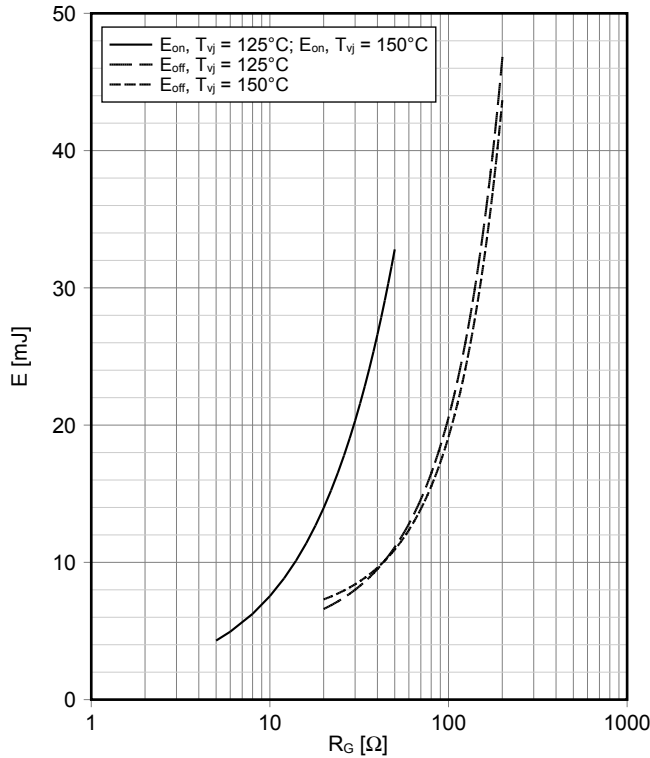
Schaltverluste IGBT, T1 / T4 (typisch)
switching losses IGBT, T1 / T4 (typical)

$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
 $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 5\ \Omega$, $R_{Goff} = 20\ \Omega$, $V_{CE} = 500\text{ V}$



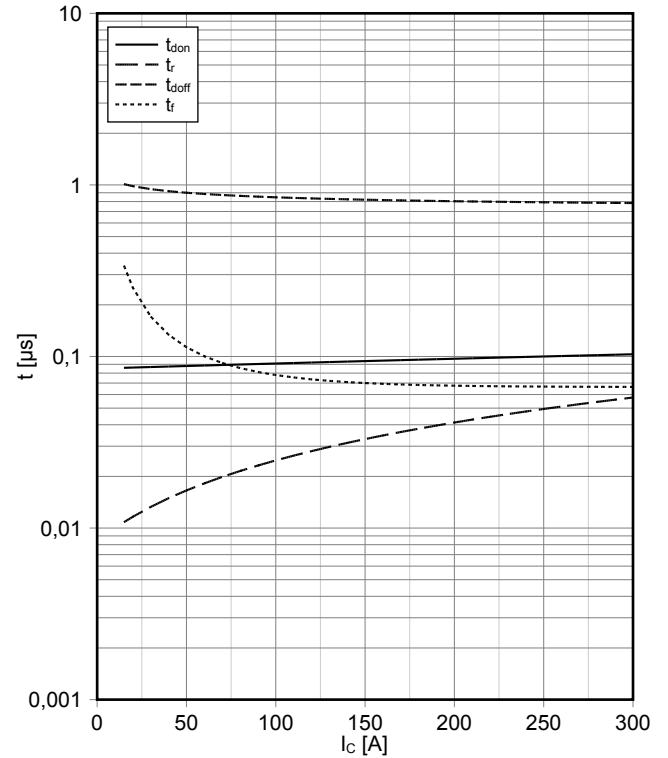
Schaltverluste IGBT, T1 / T4 (typisch)
switching losses IGBT, T1 / T4 (typical)

$E_{on} = f(R_G)$, $E_{off} = f(R_G)$
 $V_{GE} = \pm 15\text{ V}$, $I_C = 150\text{ A}$, $V_{CE} = 500\text{ V}$



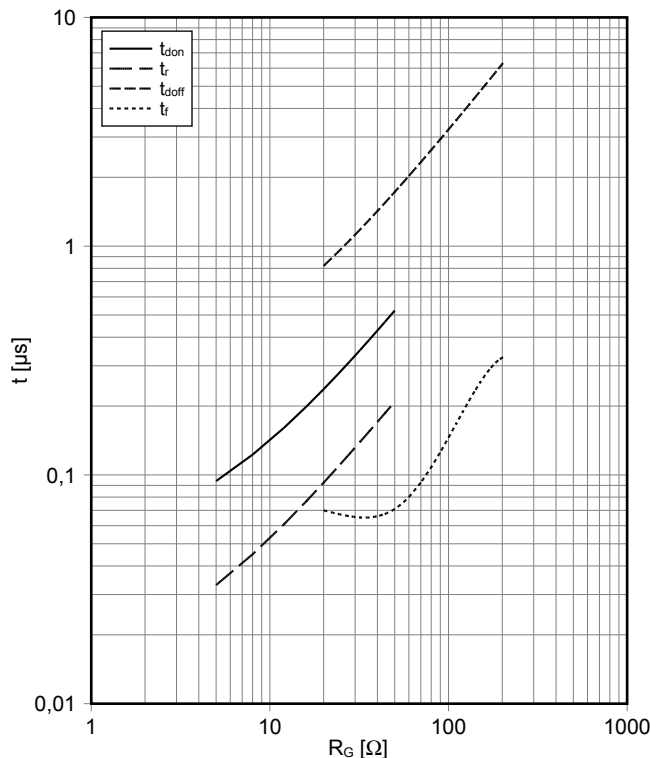
Schaltzeiten IGBT, T1 / T4 (typisch)
switching times IGBT, T1 / T4 (typical)

$t_{don} = f(I_C)$, $t_r = f(I_C)$, $t_{doff} = f(I_C)$, $t_f = f(I_C)$
 $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 5\ \Omega$, $R_{Goff} = 20\ \Omega$, $V_{CE} = 500\text{ V}$, $T_{vj} = 150^\circ\text{C}$



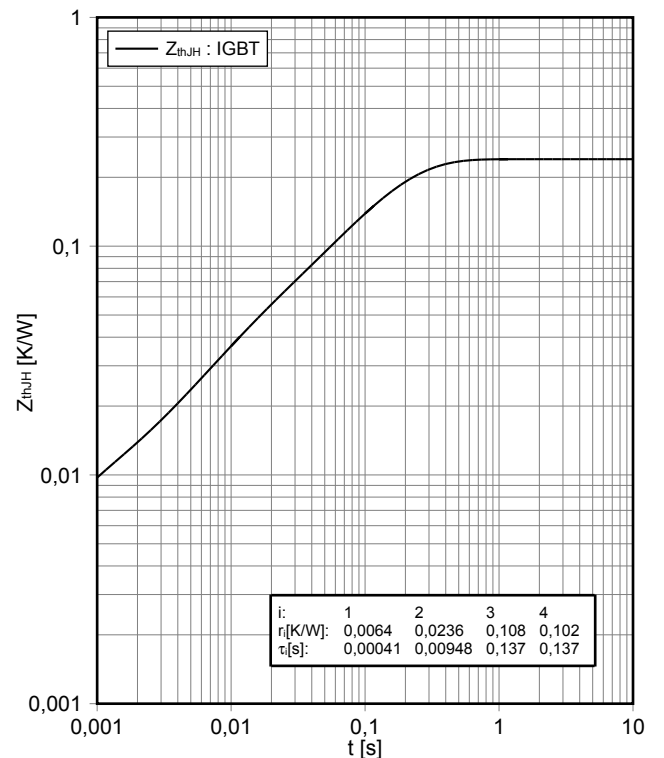
Schaltzeiten IGBT, T1 / T4 (typisch)
switching times IGBT, T1 / T4 (typical)

$t_{don} = f(R_G)$, $t_r = f(R_G)$, $t_{doff} = f(R_G)$, $t_f = f(R_G)$
 $V_{GE} = \pm 15\text{ V}$, $I_C = 150\text{ A}$, $V_{CE} = 500\text{ V}$, $T_{vj} = 150^\circ\text{C}$



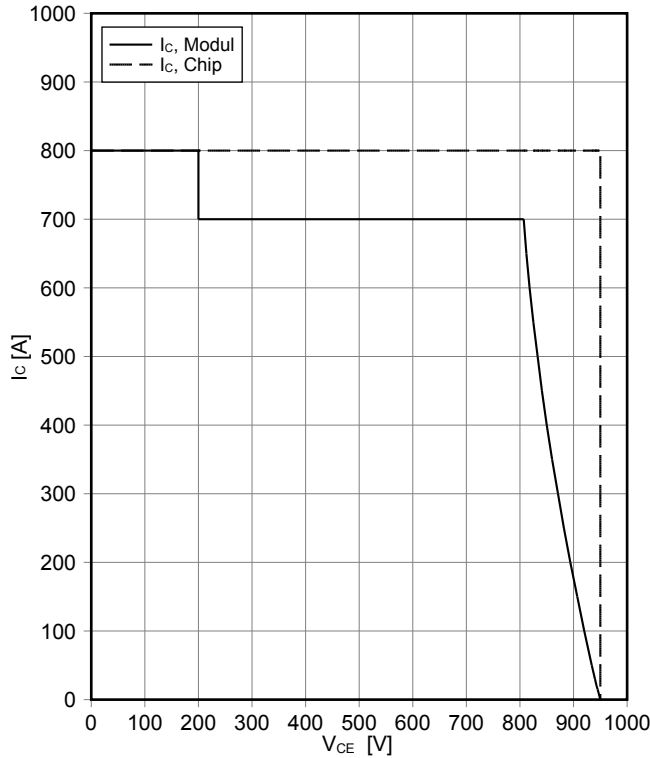
Transienter Wärmewiderstand IGBT, T1 / T4
transient thermal impedance IGBT, T1 / T4

$Z_{thJH} = f(t)$



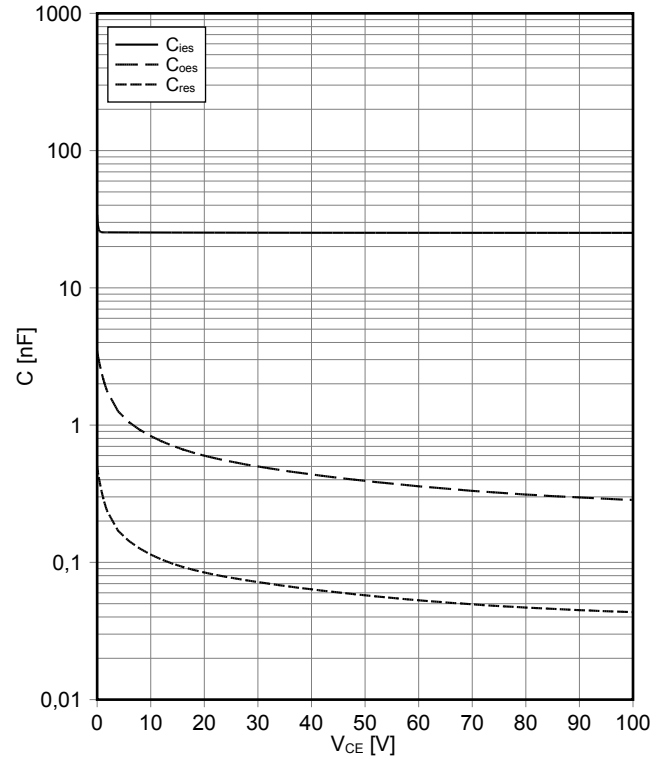
Sicherer Rückwärts-Arbeitsbereich IGBT, T1 / T4 (RBSOA)
reverse bias safe operating area IGBT, T1 / T4 (RBSOA)

$I_C = f(V_{CE})$
 $V_{GE} = \pm 15 \text{ V}$, $R_{Goff} = 20 \Omega$, $T_{vj} = 150^\circ\text{C}$



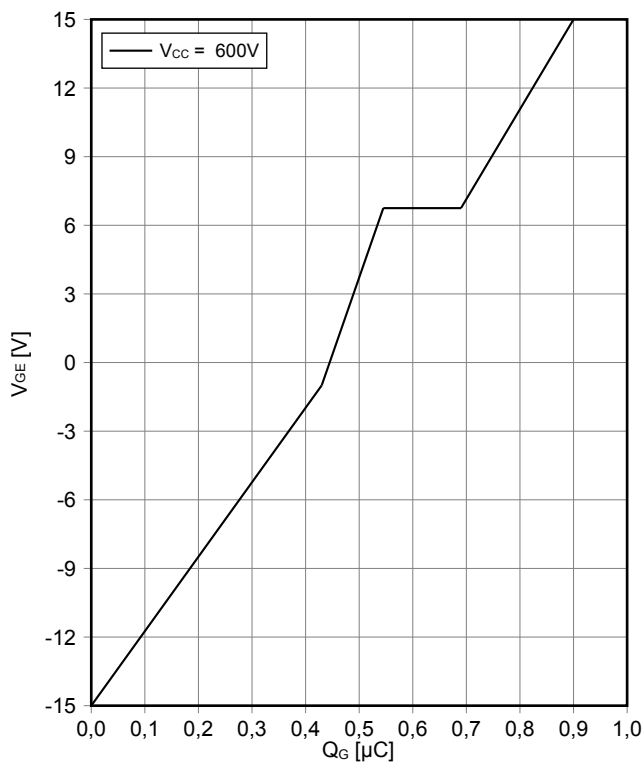
Kapazitäts Charakteristik IGBT, T1 / T4 (typisch)
capacity characteristic IGBT, T1 / T4 (typical)

$C = f(V_{CE})$
 $V_{GE} = 0 \text{ V}$, $T_{vj} = 25^\circ\text{C}$, $f = 100\text{kHz}$



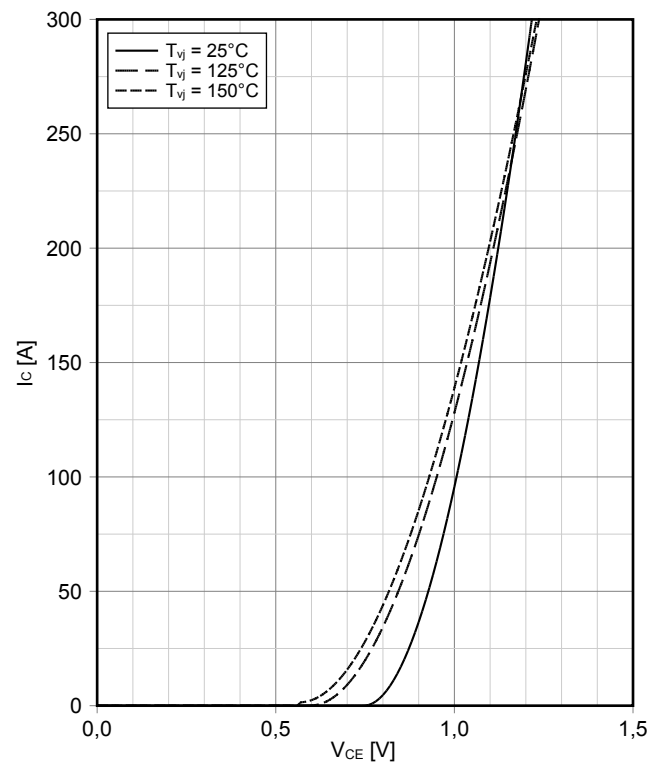
Gateladungs Charakteristik IGBT, T1 / T4 (typisch)
gate charge characteristic IGBT, T1 / T4 (typical)

$V_{GE} = f(Q_G)$
 $I_C = 400 \text{ A}$, $T_{vj} = 25^\circ\text{C}$



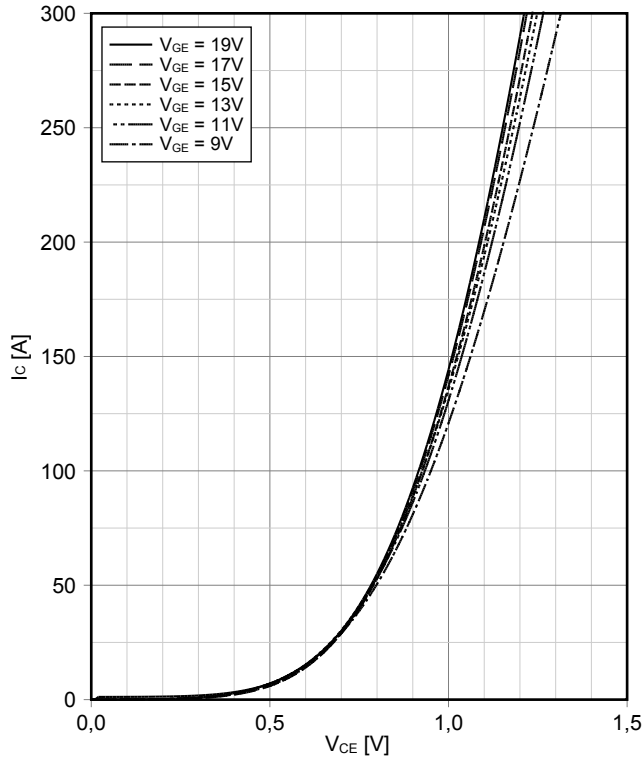
Ausgangskennlinie IGBT, T2 / T3 (typisch)
output characteristic IGBT, T2 / T3 (typical)

$I_C = f(V_{CE})$
 $V_{GE} = 15 \text{ V}$



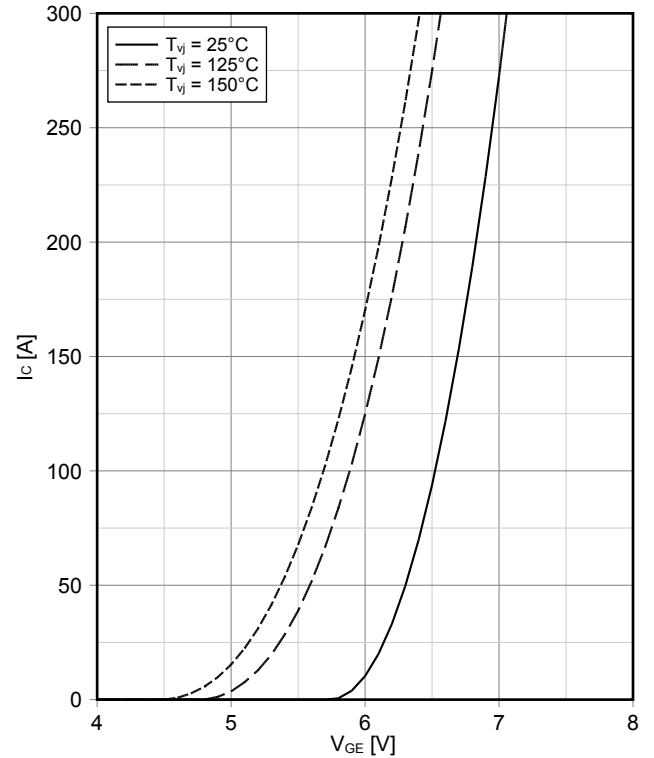
Ausgangskennlinienfeld IGBT, T2 / T3 (typisch)
output characteristic IGBT, T2 / T3 (typical)

$I_C = f(V_{CE})$
 $T_{vj} = 150^\circ\text{C}$



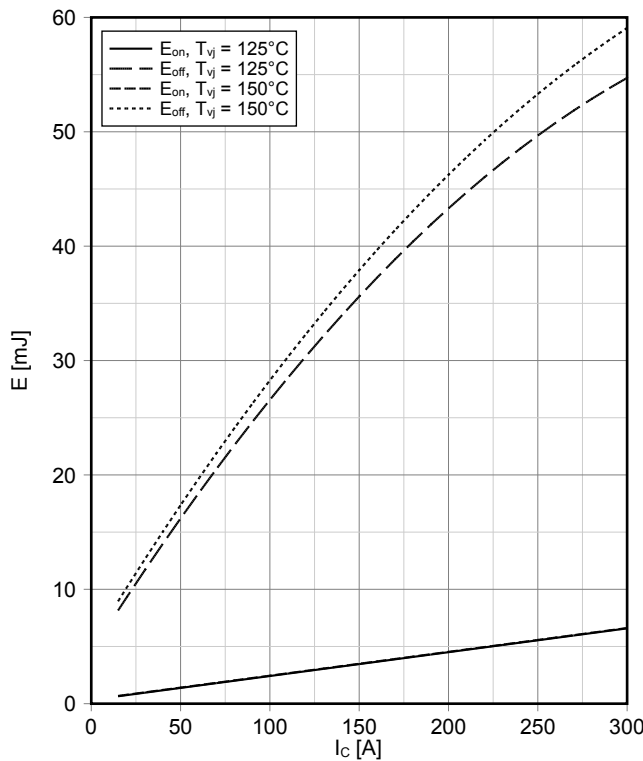
Übertragungscharakteristik IGBT, T2 / T3 (typisch)
transfer characteristic IGBT, T2 / T3 (typical)

$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



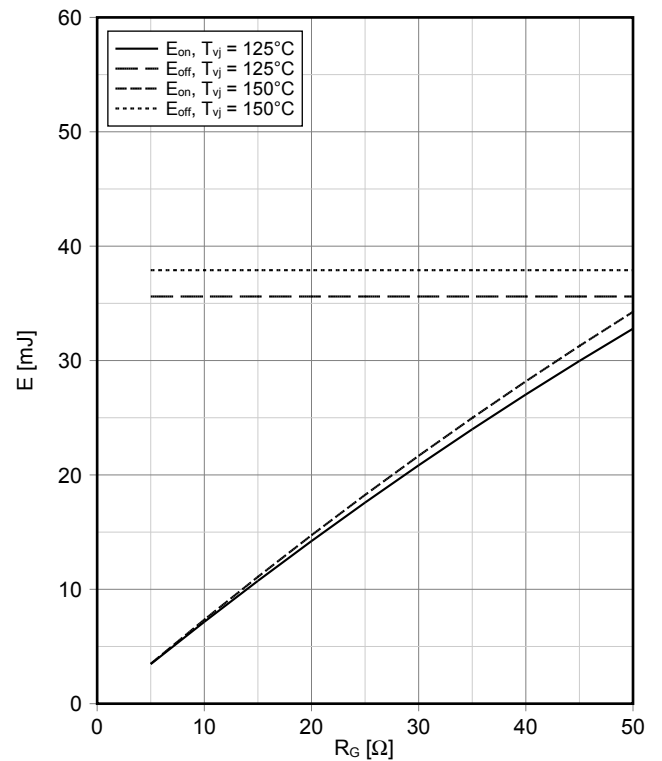
Schaltverluste IGBT, T2 / T3 (typisch)
switching losses IGBT, T2 / T3 (typical)

$E_{on} = f(I_C), E_{off} = f(I_C)$
 $V_{GE} = \pm 15\text{ V}, R_{Gon} = 5\ \Omega, R_{Goff} = 5\ \Omega, V_{CE} = 500\text{ V}$



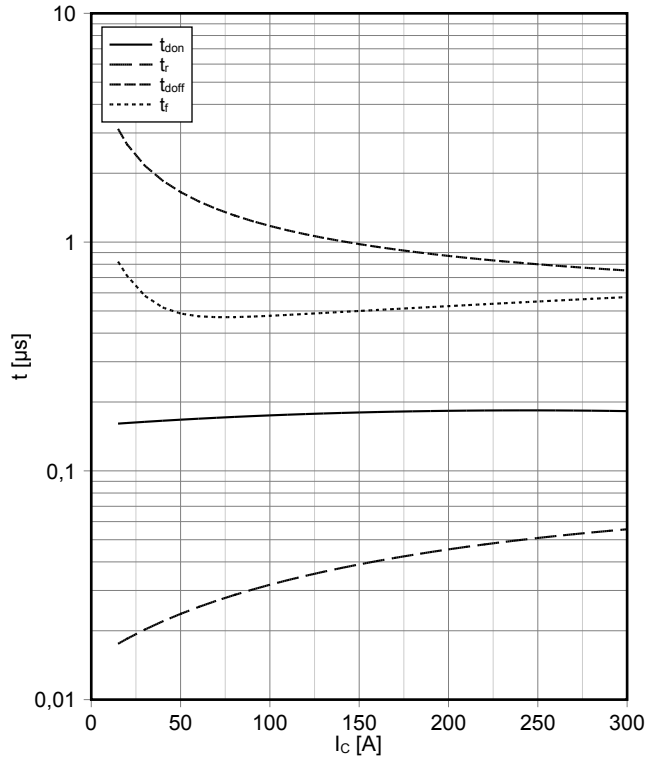
Schaltverluste IGBT, T2 / T3 (typisch)
switching losses IGBT, T2 / T3 (typical)

$E_{on} = f(R_G), E_{off} = f(R_G)$
 $V_{GE} = \pm 15\text{ V}, I_C = 150\text{ A}, V_{CE} = 500\text{ V}$



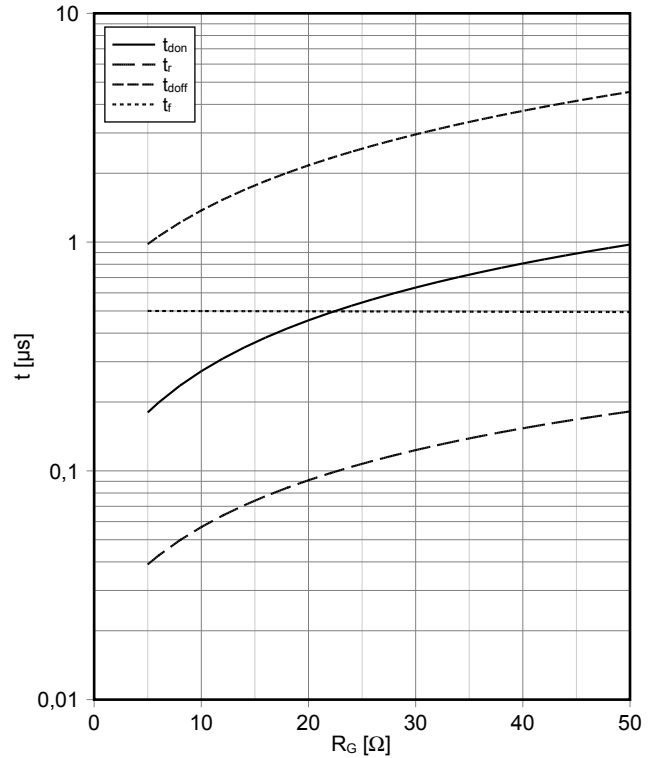
Schaltzeiten IGBT, T2 / T3 (typisch)
switching times IGBT, T2 / T3 (typical)

$t_{don} = f(I_C)$, $t_r = f(I_C)$, $t_{doff} = f(I_C)$, $t_f = f(I_C)$
 $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 5\ \Omega$, $R_{Goff} = 5\ \Omega$, $V_{CE} = 500\text{ V}$, $T_{vj} = 150^\circ\text{C}$



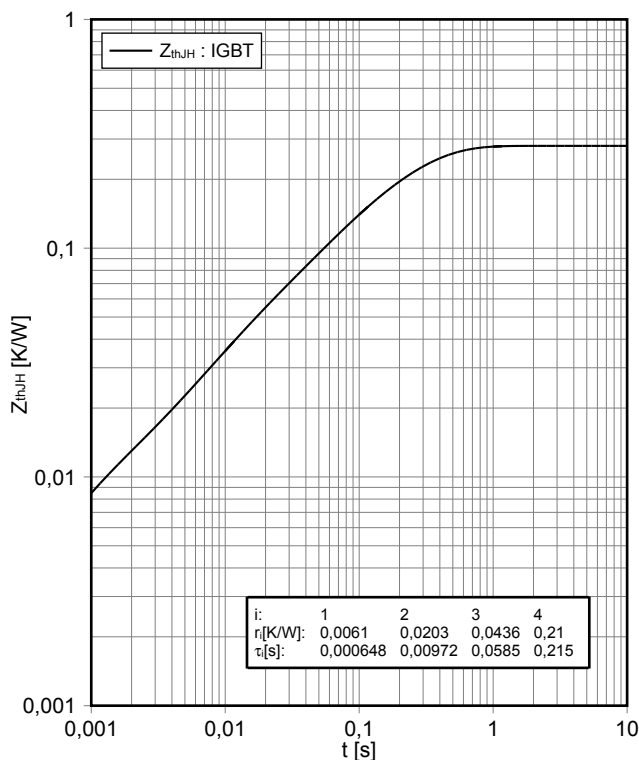
Schaltzeiten IGBT, T2 / T3 (typisch)
switching times IGBT, T2 / T3 (typical)

$t_{don} = f(R_G)$, $t_r = f(R_G)$, $t_{doff} = f(R_G)$, $t_f = f(R_G)$
 $V_{GE} = \pm 15\text{ V}$, $I_C = 150\text{ A}$, $V_{CE} = 500\text{ V}$, $T_{vj} = 150^\circ\text{C}$



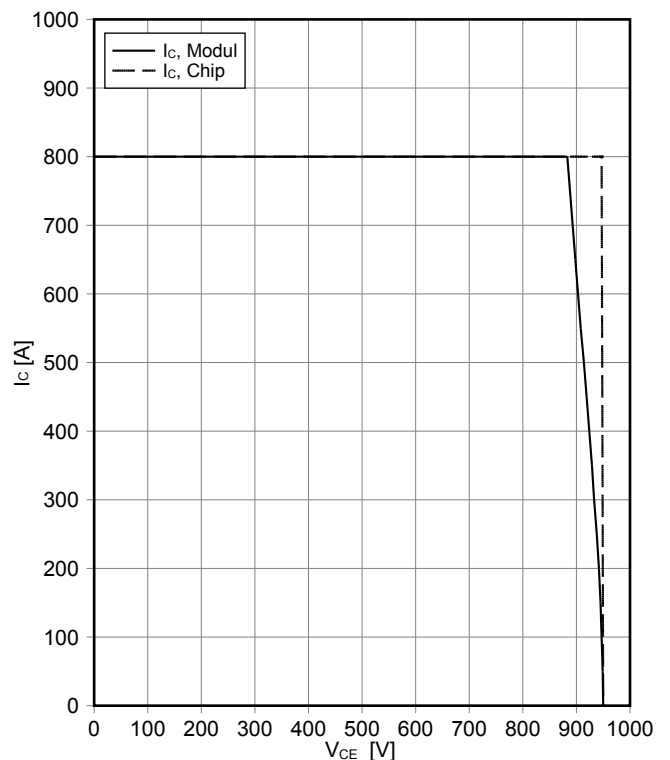
Transienter Wärmewiderstand IGBT, T2 / T3
transient thermal impedance IGBT, T2 / T3

$Z_{thJH} = f(t)$



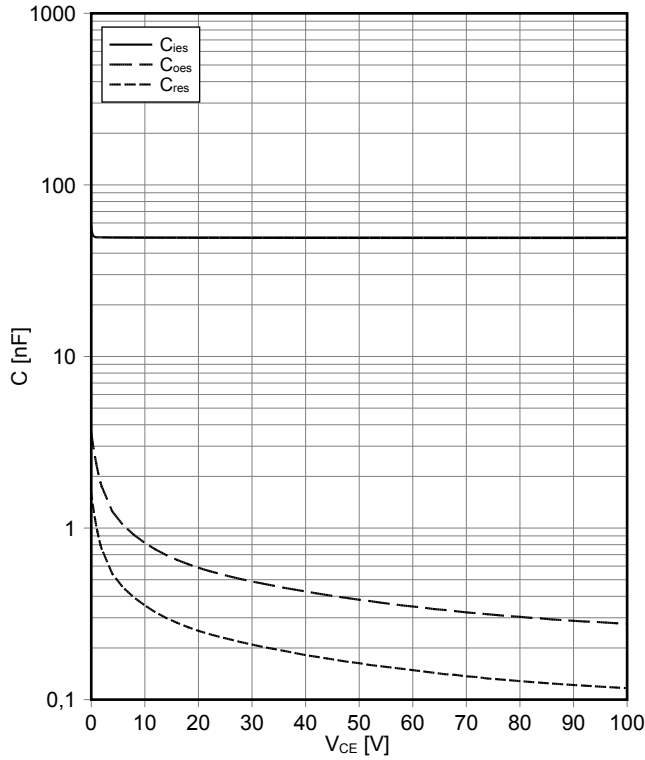
Sicherer Rückwärts-Arbeitsbereich IGBT, T2 / T3 (RBSOA)
reverse bias safe operating area IGBT, T2 / T3 (RBSOA)

$I_C = f(V_{CE})$
 $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 5\ \Omega$, $T_{vj} = 150^\circ\text{C}$



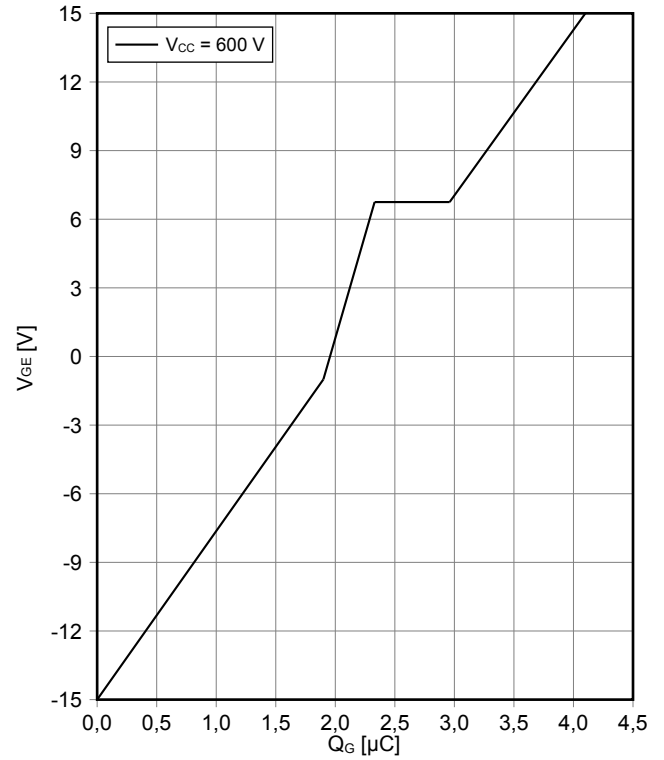
Kapazitäts Charakteristik IGBT, T2 / T3 (typisch)
capacity characteristic IGBT, T2 / T3 (typical)

$C = f(V_{CE})$
 $V_{GE} = 0 \text{ V}, T_{vj} = 25^\circ\text{C}, f = 100\text{kHz}$



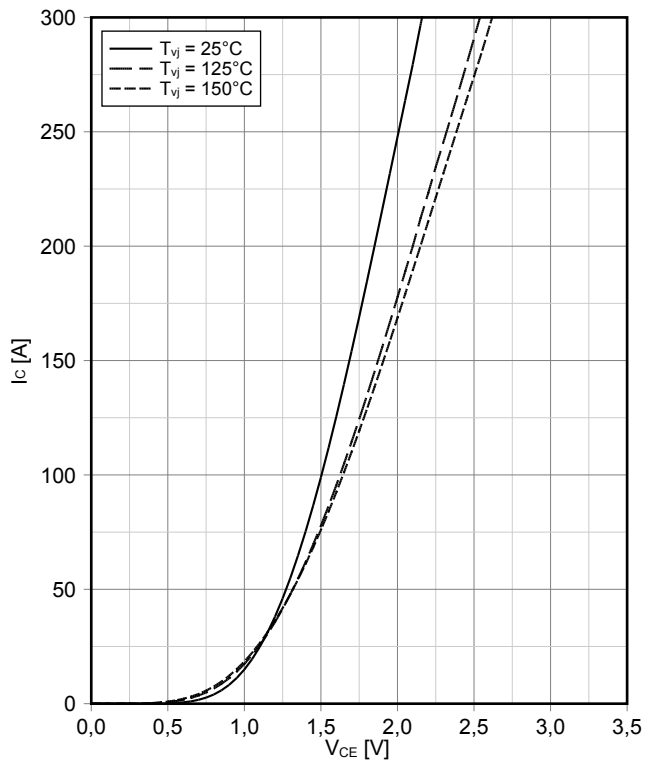
Gateladungs Charakteristik IGBT, T2 / T3 (typisch)
gate charge characteristic IGBT, T2 / T3 (typical)

$V_{GE} = f(Q_G)$
 $I_C = 400 \text{ A}, T_{vj} = 25^\circ\text{C}$



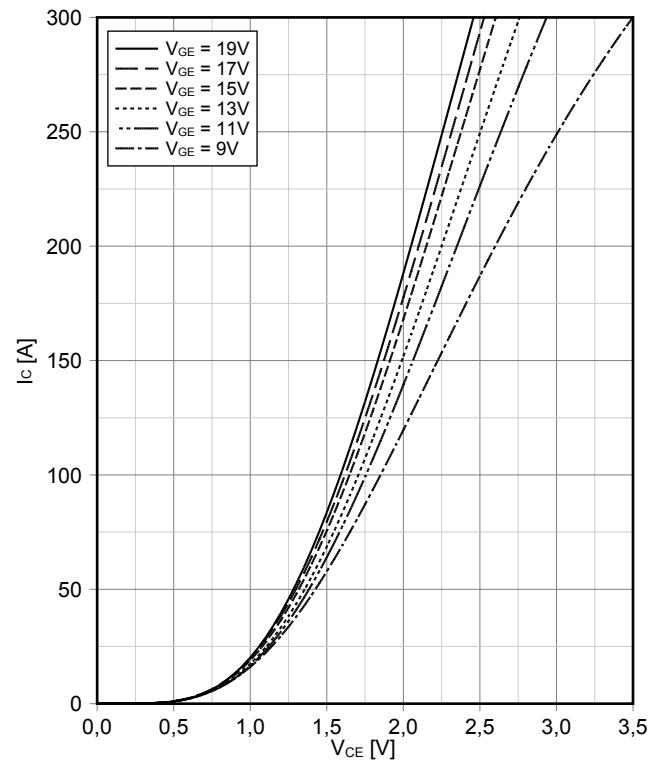
Ausgangskennlinie IGBT, T5 / T6 (typisch)
output characteristic IGBT, T5 / T6 (typical)

$I_C = f(V_{CE})$
 $V_{GE} = 15 \text{ V}$



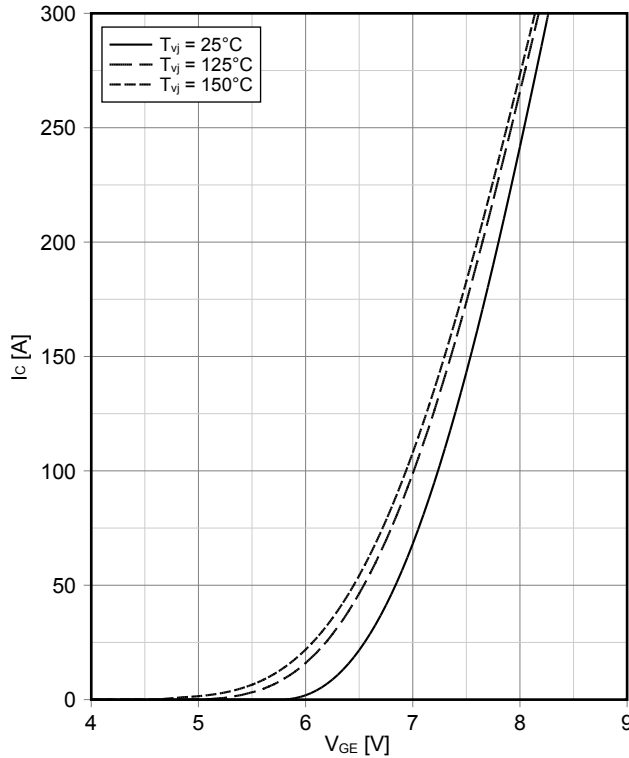
Ausgangskennlinienfeld IGBT, T5 / T6 (typisch)
output characteristic IGBT, T5 / T6 (typical)

$I_C = f(V_{CE})$
 $T_{vj} = 150^\circ\text{C}$



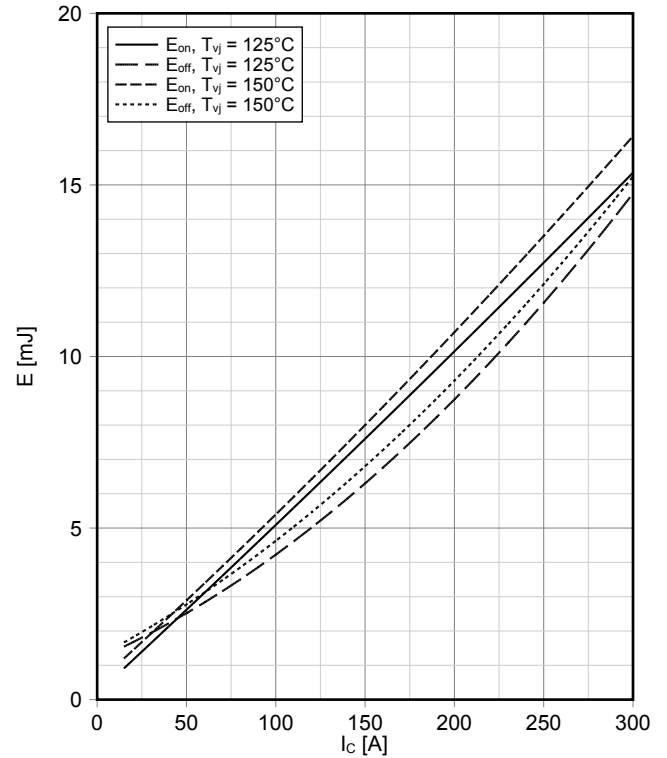
Übertragungscharakteristik IGBT, T5 / T6 (typisch)
transfer characteristic IGBT, T5 / T6 (typical)

$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



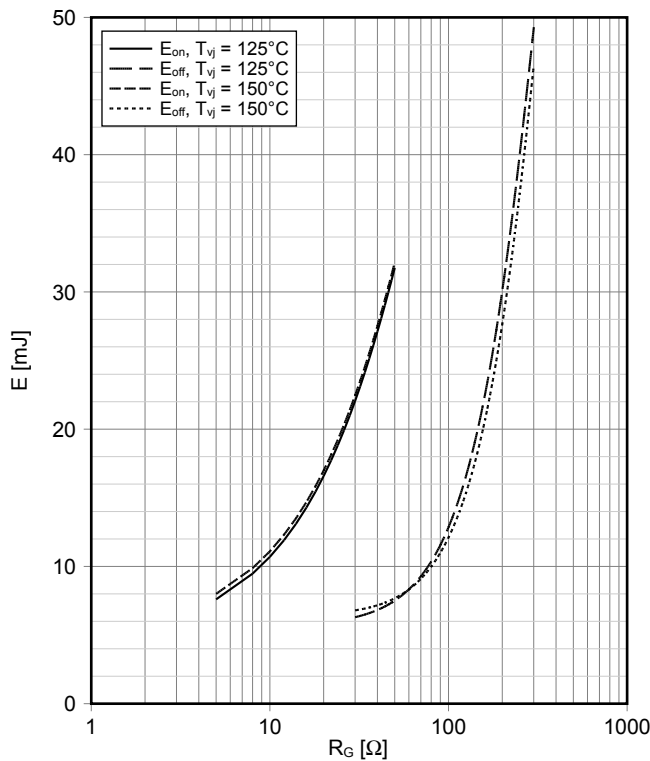
Schaltverluste IGBT, T5 / T6 (typisch)
switching losses IGBT, T5 / T6 (typical)

$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
 $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 5\ \Omega$, $R_{Goff} = 30\ \Omega$, $V_{CE} = 500\text{ V}$



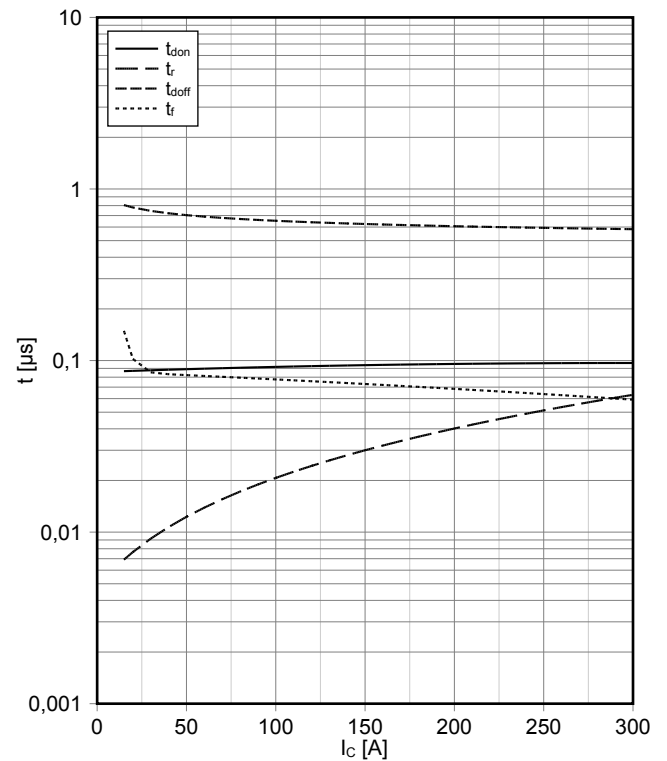
Schaltverluste IGBT, T5 / T6 (typisch)
switching losses IGBT, T5 / T6 (typical)

$E_{on} = f(R_G)$, $E_{off} = f(R_G)$
 $V_{GE} = \pm 15\text{ V}$, $I_C = 150\text{ A}$, $V_{CE} = 500\text{ V}$



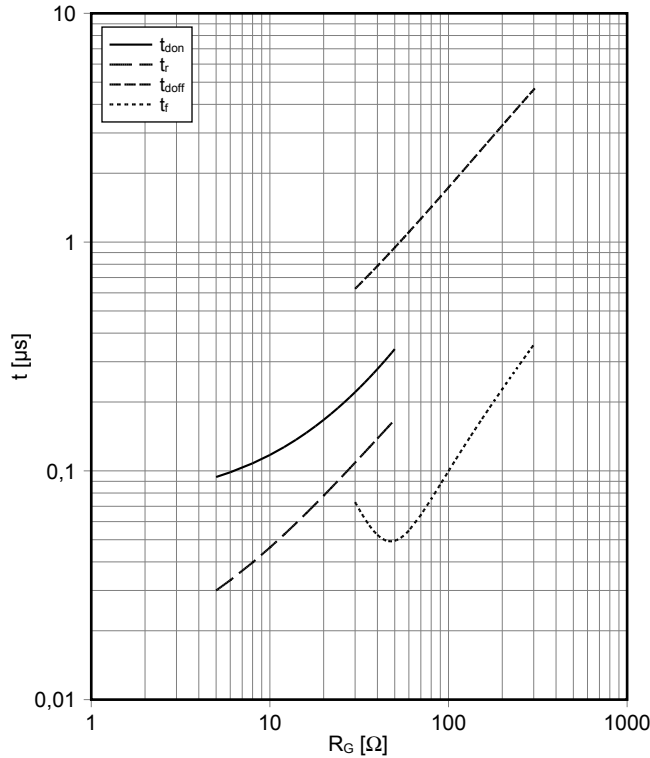
Schaltzeiten IGBT, T5 / T6 (typisch)
switching times IGBT, T5 / T6 (typical)

$t_{don} = f(I_C)$, $t_r = f(I_C)$, $t_{doff} = f(I_C)$, $t_f = f(I_C)$
 $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 5\ \Omega$, $R_{Goff} = 30\ \Omega$, $V_{CE} = 500\text{ V}$, $T_{vj} = 150^\circ\text{C}$



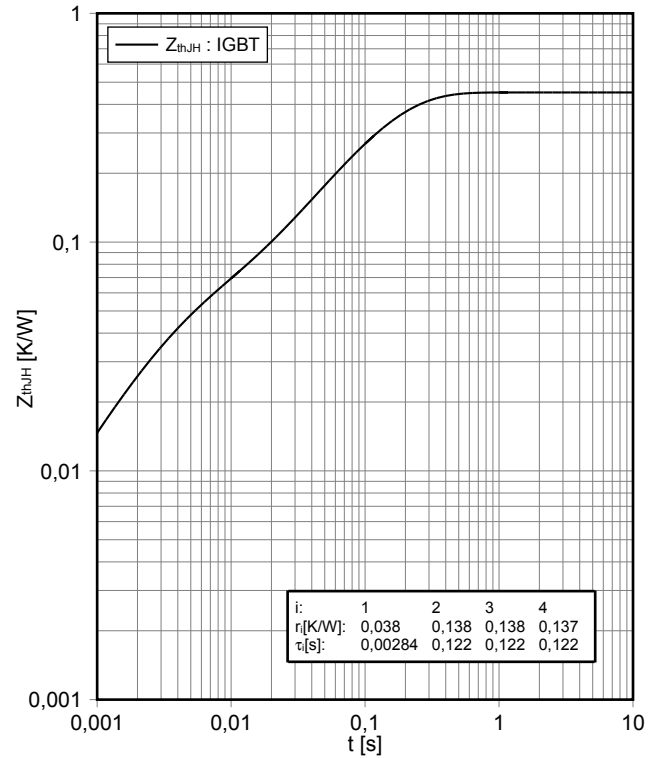
Schaltzeiten IGBT, T5 / T6 (typisch) switching times IGBT, T5 / T6 (typical)

$t_{don} = f(R_G)$, $t_r = f(R_G)$, $t_{doff} = f(R_G)$, $t_f = f(R_G)$
 $V_{GE} = \pm 15\text{ V}$, $I_C = 150\text{ A}$, $V_{CE} = 500\text{ V}$, $T_{vj} = 150^\circ\text{C}$



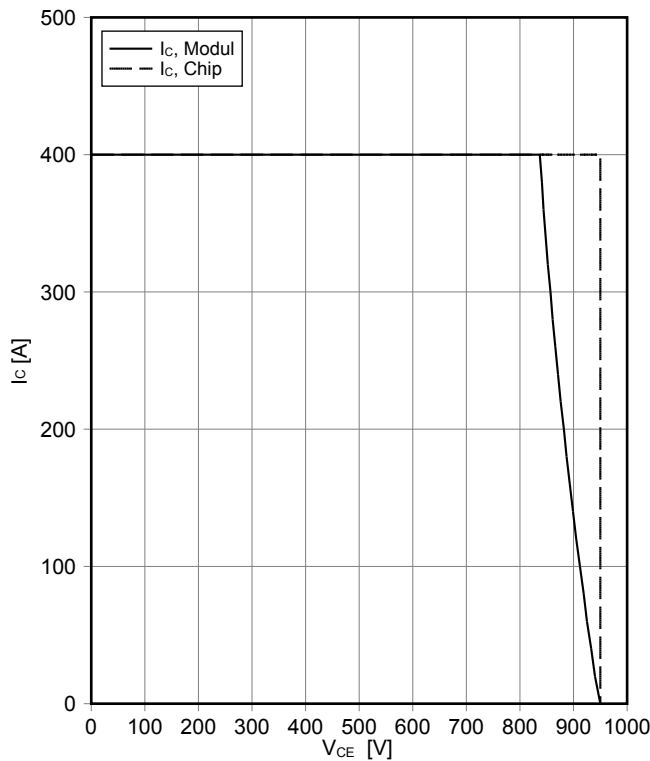
Transienter Wärmewiderstand IGBT, T5 / T6 transient thermal impedance IGBT, T5 / T6

$Z_{thJH} = f(t)$



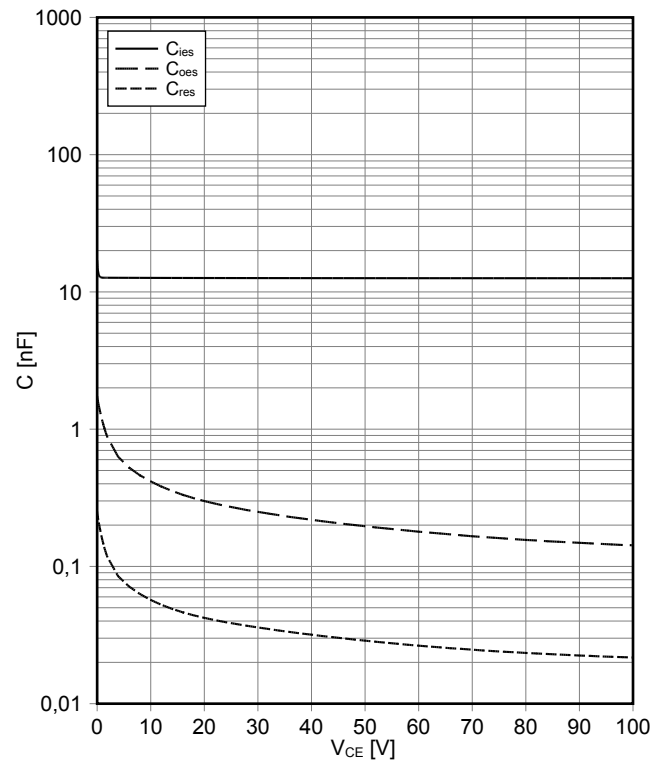
Sicherer Rückwärts-Arbeitsbereich IGBT, T5 / T6 (RBSOA) reverse bias safe operating area IGBT, T5 / T6 (RBSOA)

$I_C = f(V_{CE})$
 $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 30\ \Omega$, $T_{vj} = 150^\circ\text{C}$



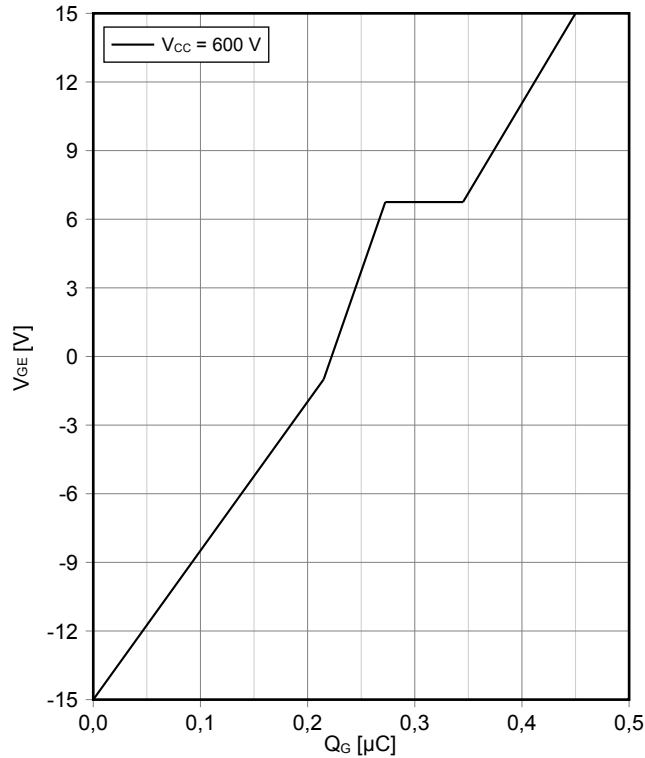
Kapazitäts Charakteristik IGBT, T5 / T6 (typisch) capacity characteristic IGBT, T5 / T6 (typical)

$C = f(V_{CE})$
 $V_{GE} = 0\text{ V}$, $T_{vj} = 25^\circ\text{C}$, $f = 100\text{ kHz}$



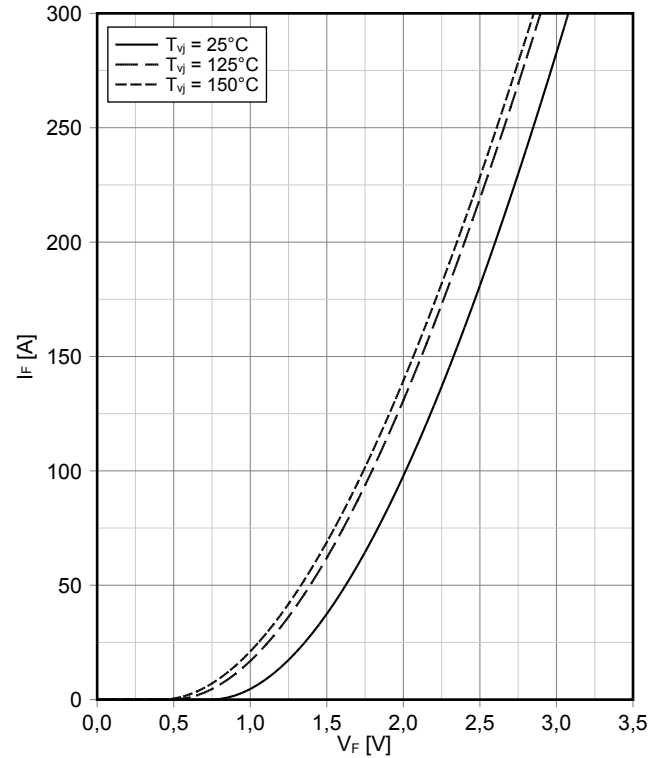
Gateladungs Charakteristik IGBT, T5 / T6 (typisch)
gate charge characteristic IGBT, T5 / T6 (typical)

$V_{GE} = f(Q_G)$
 $I_C = 200\text{ A}, T_{vj} = 25^\circ\text{C}$



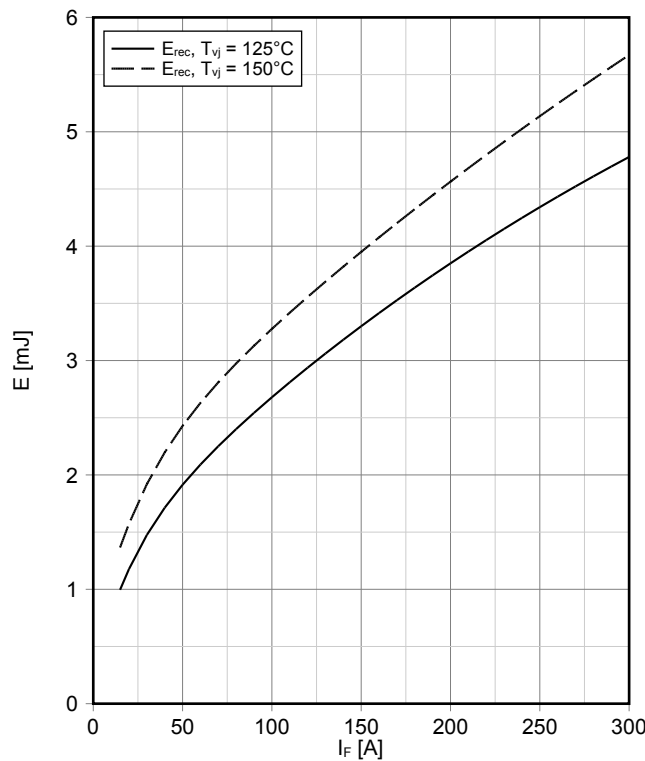
Durchlasskennlinie der Diode, D1 / D4 (typisch)
forward characteristic of Diode, D1 / D4 (typical)

$I_F = f(V_F)$



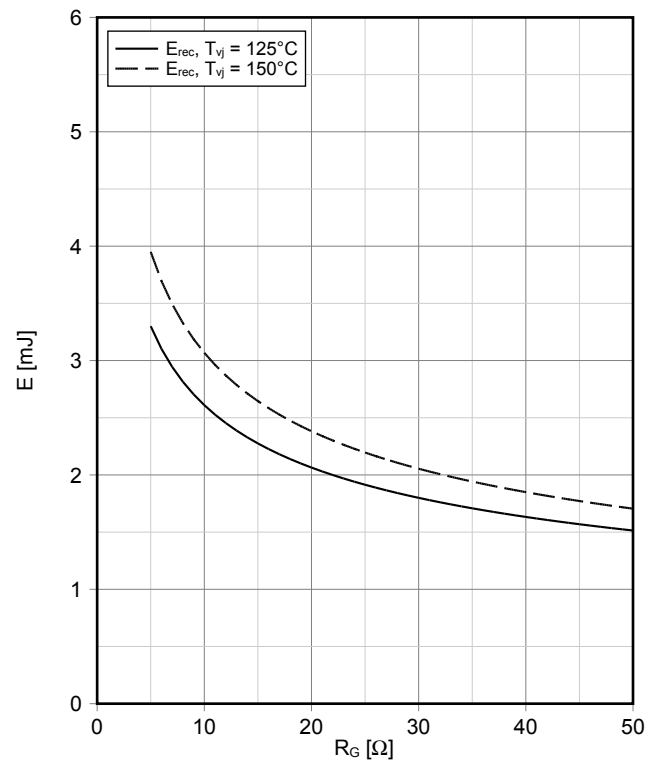
Schaltverluste Diode, D1 / D4 (typisch)
switching losses Diode, D1 / D4 (typical)

$E_{rec} = f(I_F)$
 $R_{Gon} = 5\ \Omega, V_{CE} = 500\text{ V}$

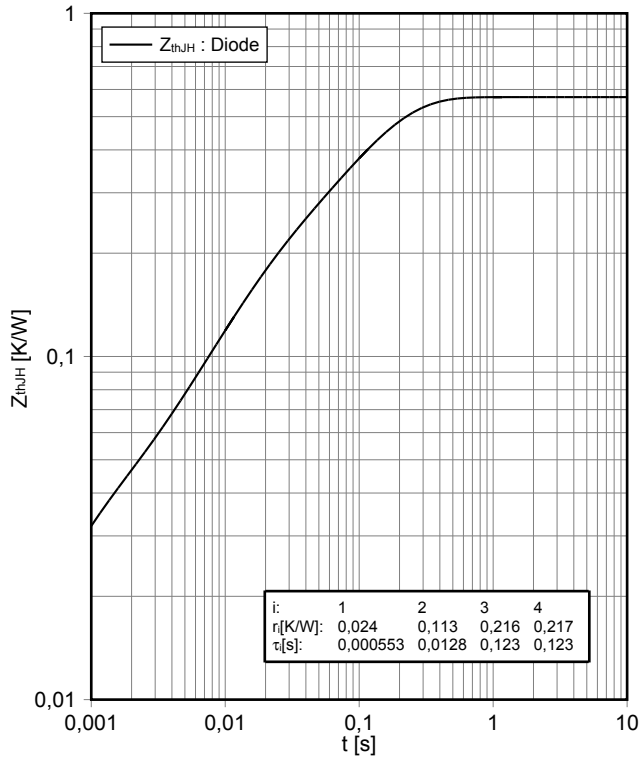


Schaltverluste Diode, D1 / D4 (typisch)
switching losses Diode, D1 / D4 (typical)

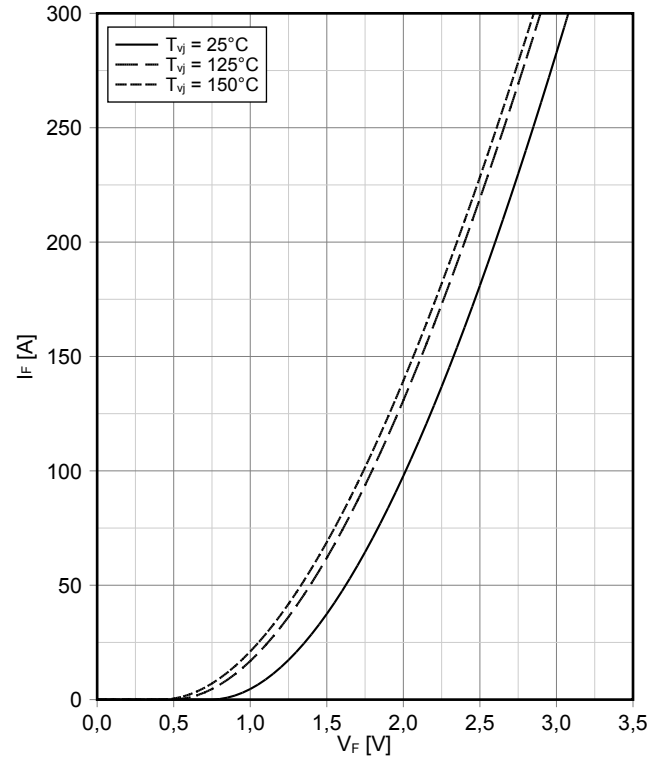
$E_{rec} = f(R_G)$
 $I_F = 150\text{ A}, V_{CE} = 500\text{ V}$



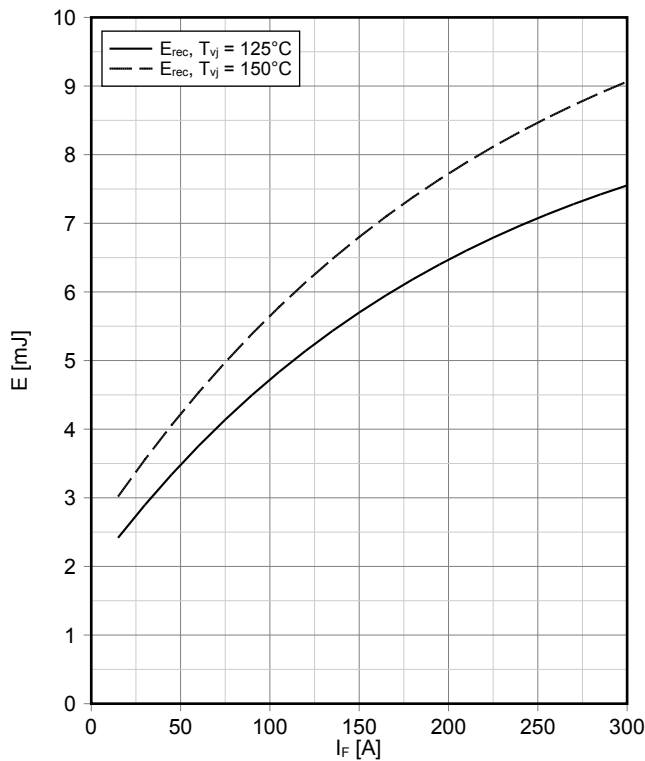
Transienter Wärmewiderstand Diode, D1 / D4
transient thermal impedance Diode, D1 / D4
 $Z_{thJH} = f(t)$



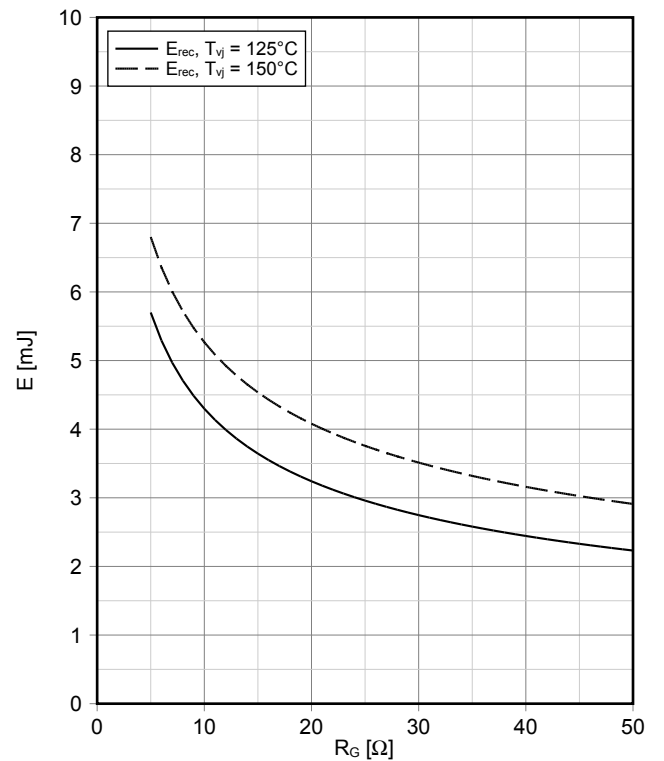
Durchlasskennlinie der Diode, D2 / D3 (typisch)
forward characteristic of Diode, D2 / D3 (typical)
 $I_F = f(V_F)$



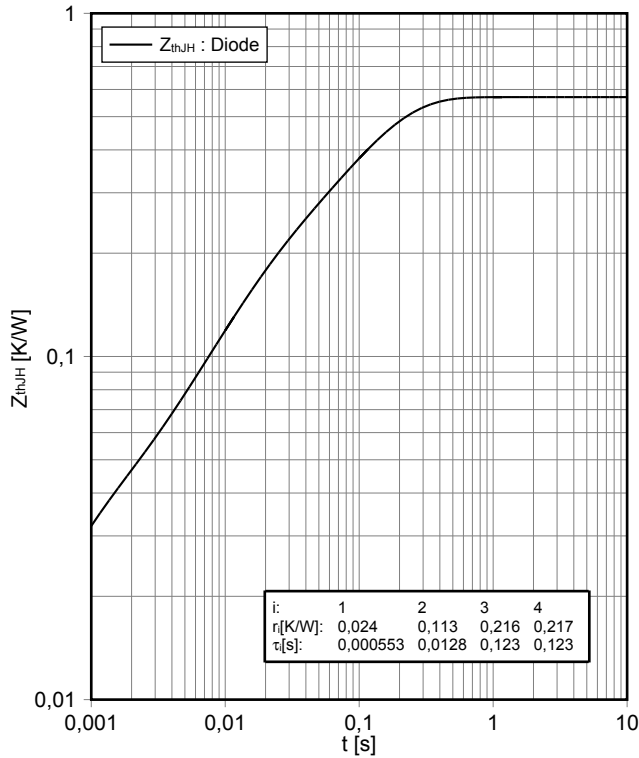
Schaltverluste Diode, D2 / D3 (typisch)
switching losses Diode, D2 / D3 (typical)
 $E_{rec} = f(I_F)$
 $R_{Gon} = 5 \Omega, V_{CE} = 500 V$



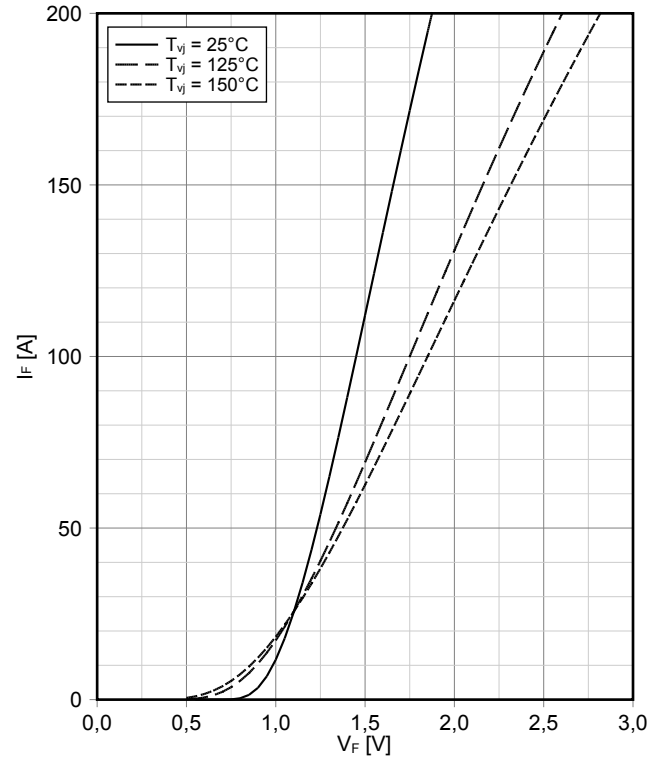
Schaltverluste Diode, D2 / D3 (typisch)
switching losses Diode, D2 / D3 (typical)
 $E_{rec} = f(R_G)$
 $I_F = 150 A, V_{CE} = 500 V$



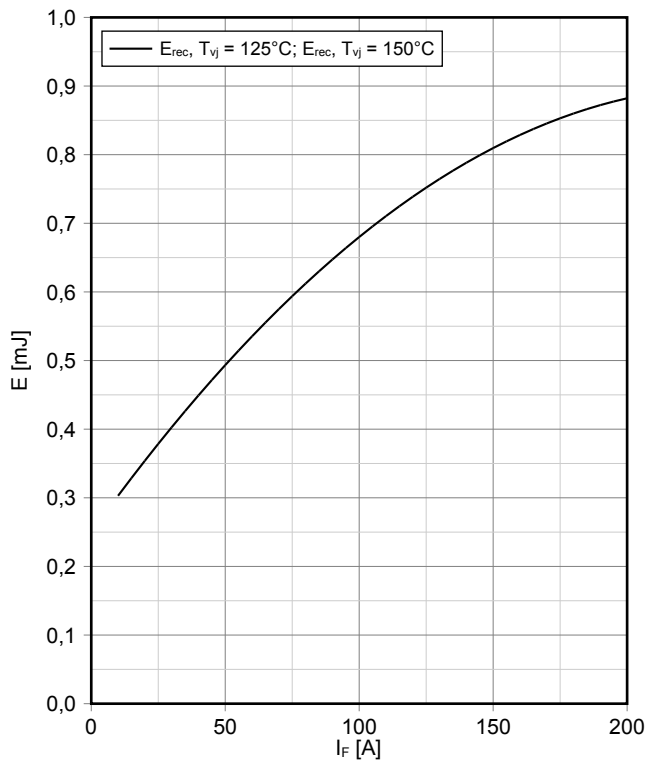
Transienter Wärmewiderstand Diode, D2 / D3
transient thermal impedance Diode, D2 / D3
 $Z_{thJH} = f(t)$



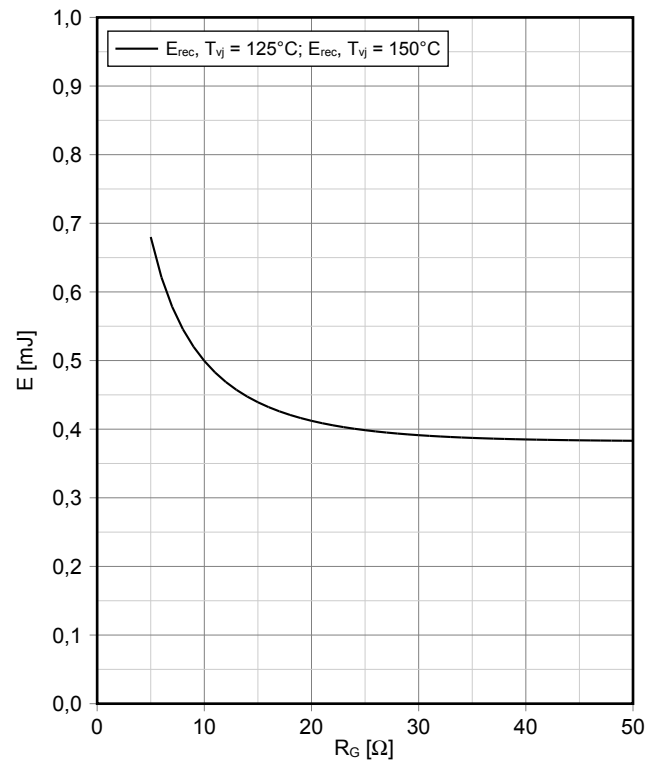
Durchlasskennlinie der Diode, D5-D6 (typisch)
forward characteristic of Diode, D5-D6 (typical)
 $I_F = f(V_F)$



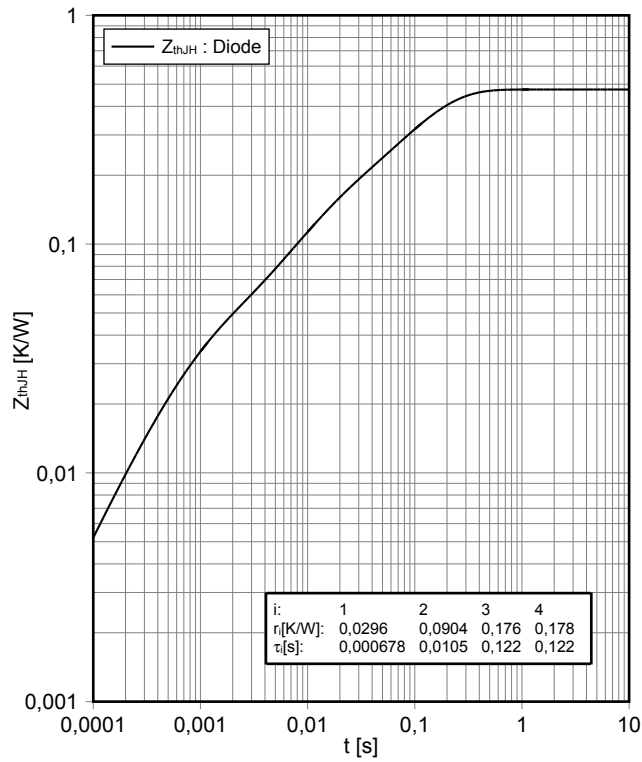
Schaltverluste Diode, D5-D6 (typisch)
switching losses Diode, D5-D6 (typical)
 $E_{rec} = f(I_F)$
 $R_{Gon} = 5 \Omega, V_{CE} = 500 V$



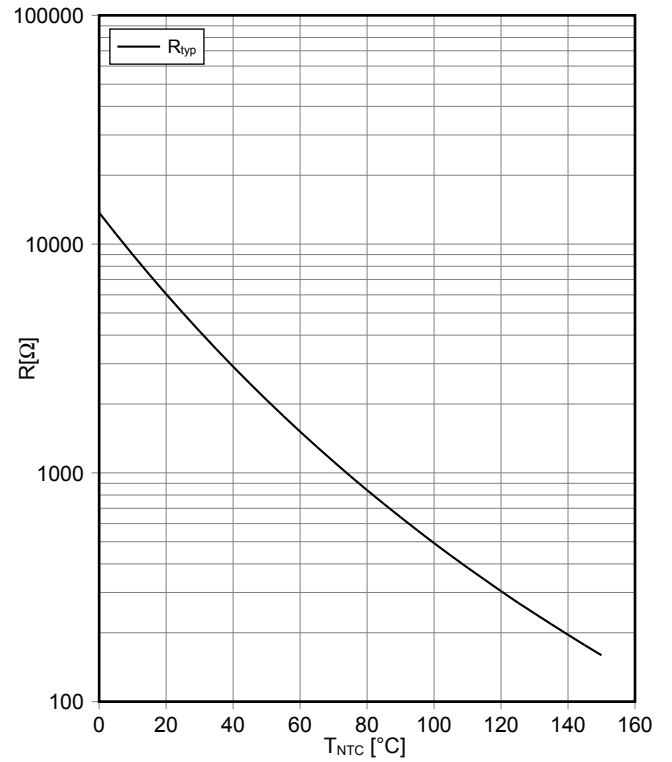
Schaltverluste Diode, D5-D6 (typisch)
switching losses Diode, D5-D6 (typical)
 $E_{rec} = f(R_G)$
 $I_F = 100 A, V_{CE} = 500 V$



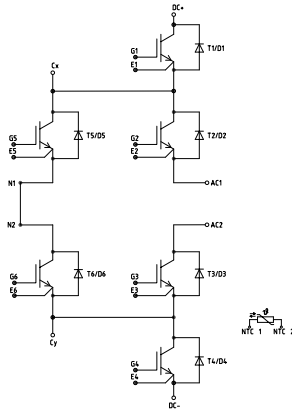
Transienter Wärmewiderstand Diode, D5-D6
transient thermal impedance Diode, D5-D6
 $Z_{thJH} = f(t)$



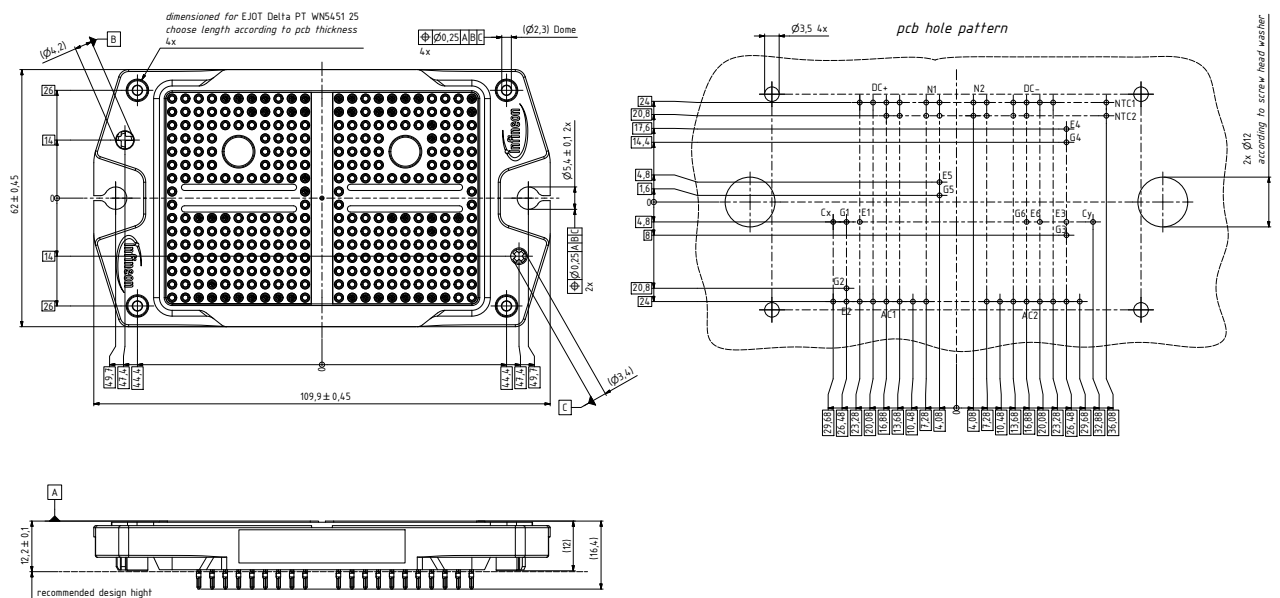
NTC-Widerstand-Temperaturkennlinie (typisch)
NTC-Thermistor-temperature characteristic (typical)
 $R = f(T)$



Schaltplan / Circuit diagram



Gehäuseabmessungen / Package outlines



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